

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R _{thJS}		K/W
BCR112		≤ 240	
BCR112W		≤ 105	

¹For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)

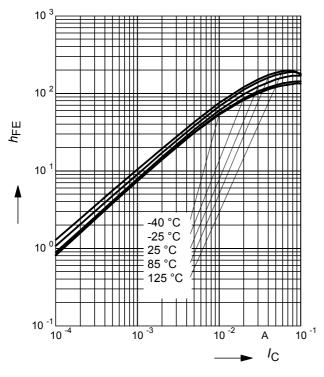
Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics				1	
Collector-emitter breakdown voltage	V _{(BR)CEO}	50	-	-	V
<i>I</i> _C = 100 μA, <i>I</i> _B = 0					
Collector-base breakdown voltage	V _{(BR)CBO}	50	-	-	
$I_{\rm C}$ = 10 µA, $I_{\rm E}$ = 0					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB}$ = 40 V, $I_{\rm E}$ = 0					
Emitter-base cutoff current	I _{EBO}	-	-	1.61	mA
V _{EB} = 10 V, <i>I</i> _C = 0					
DC current gain ¹⁾	h _{FE}	20	-	-	-
<i>I</i> _C = 5 mA, <i>V</i> _{CE} = 5 V					
Collector-emitter saturation voltage ¹⁾	V _{CEsat}	-	-	0.3	V
<i>I</i> _C = 10 mA, <i>I</i> _B = 0.5 mA					
Input off voltage	V _{i(off)}	0.8	-	1.5	
<i>I</i> _C = 100 μA, <i>V</i> _{CE} = 5 V					
Input on voltage	V _{i(on)}	1	-	2.5	
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 0.3 V					
Input resistor	<i>R</i> ₁	3.2	4.7	6.2	kΩ
Resistor ratio	R ₁ /R ₂	0.9	1	1.1	-
AC Characteristics					
Transition frequency	f _T	-	140	-	MHz
<i>I</i> _C = 10 mA, <i>V</i> _{CE} = 5 V, <i>f</i> = 100 MHz					
Collector-base capacitance	C _{cb}	-	3	-	pF
V _{CB} = 10 V, <i>f</i> = 1 MHz					
			•	•	•

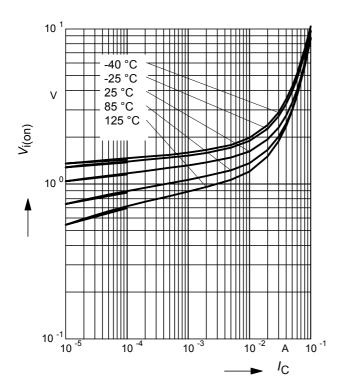
¹Pulse test: t < 300 μ s; D < 2%



DC current gain $h_{FE} = f(I_C)$ $V_{CE} = 5 V$ (common emitter configuration)

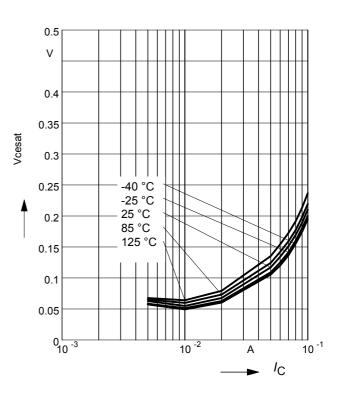


Input on Voltage $V_{i(on)} = f(I_C)$ $V_{CE} = 0.3V$ (common emitter configuration)

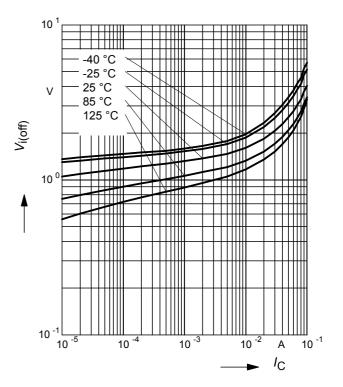


Collector-emitter saturation voltage

 $V_{\text{CEsat}} = f(I_{\text{C}}), I_{\text{C}}/I_{\text{B}} = 20$

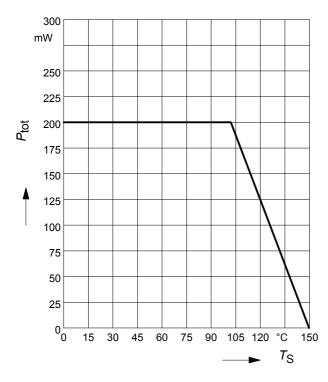


Input off voltage $V_{i(off)} = f(I_C)$ $V_{CE} = 5V$ (common emitter configuration)

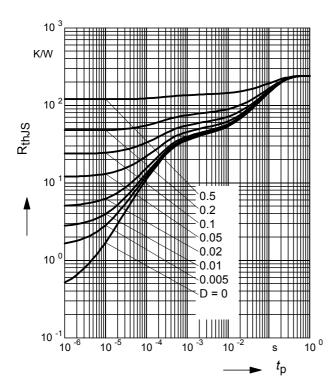




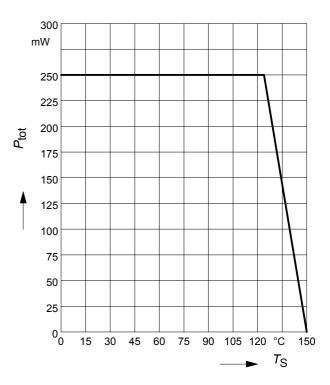
Total power dissipation $P_{tot} = f(T_S)$ BCR112



Permissible Pulse Load $R_{thJS} = f(t_p)$ BCR112

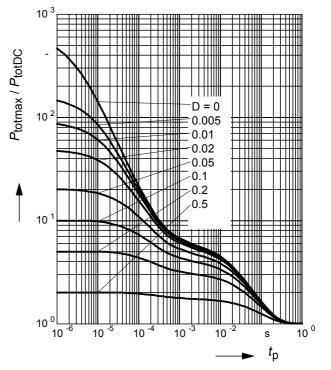


Total power dissipation $P_{tot} = f(T_S)$ BCR112W



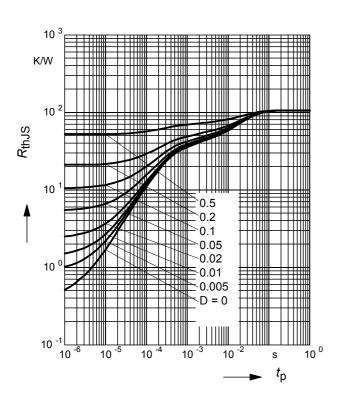
Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{\text{p}})$ BCR112



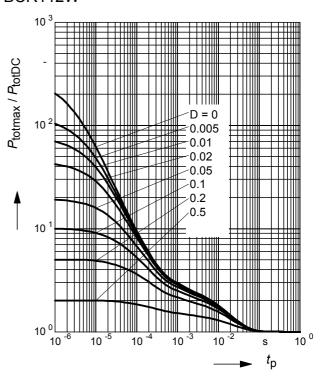


Permissible Puls Load $R_{thJS} = f(t_p)$ BCR112W

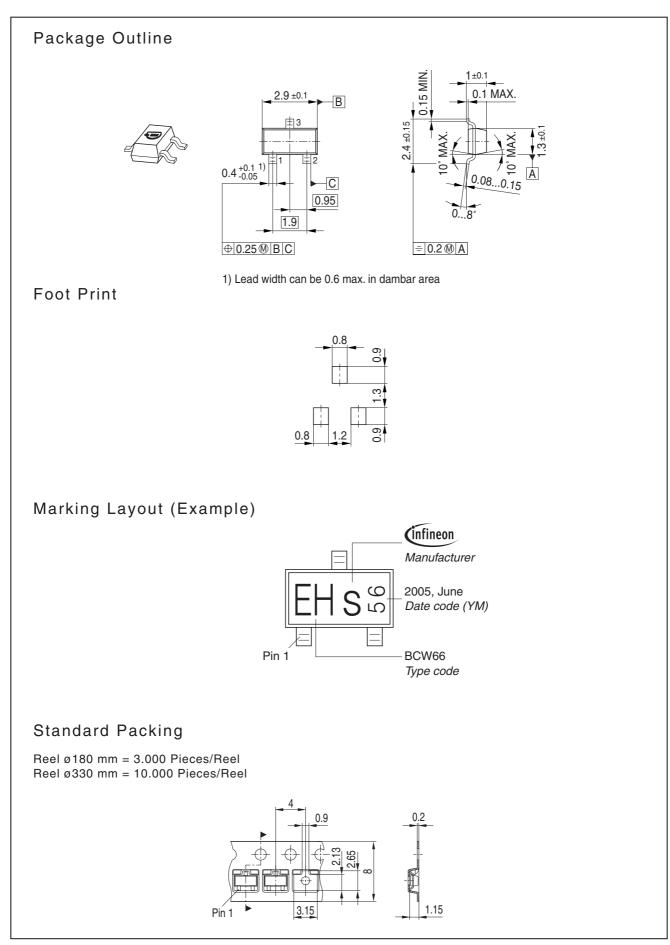


Permissible Pulse Load

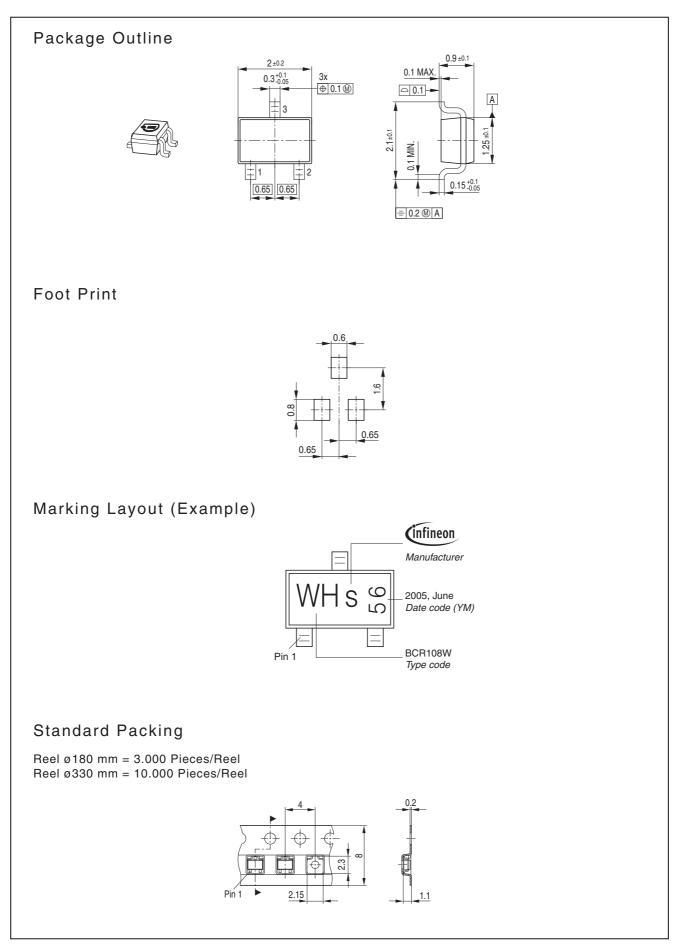
















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